Atty Docket No.: JCLA8066 Serial No.: 10/065,380

REMARKS

Response to 35 U.S.C. 121

The Examiner issued a restriction requirement. According to the Office Action, Group I: claims 1-10 are drawn to a semiconductor device classified in class 257, subclass 304 and 306, Group II: claims 11-16 are drawn to a process of making a semiconductor device, classified in class 438, subclass 244. According to the Office Action, the two groups of inventions are distinct and a restriction to one of two inventions is required under 35 U.S.C. 121.

Applicants elect **Group I** and cancel claims 9-15 without prejudice, waiver, or disclaimer, and amend the TITLE, accordingly. Applicants respectfully bring the Examiner's attention to incorrectly group the claim 16 into Group II because the claim 16 is apparently a semiconductor device classified in the same class of Group I. Applicants respectfully request the Examiner to group the claim 16 into elected Group I for prosecution in the application. Applicants also add new claims 17 and 18 for further prosecution. Applicants also reserve the right to purse the subject matter of the non-elected claims in a divisional application if Applicants so choose.

Upon entry of the amendments, claims 1-6, 8 and 16-18 are pending in the present application. More specifically, claims 1-6 and 8 are directly amended; claims 7, and 9-15 are canceled without prejudice, waiver, or disclaimer; and claims 17-18 are newly added. These amendments and additions are specifically described hereinafter. It is believed that the foregoing amendments and additions add no new matter to the present application.

An early examination and allowance of the present application is solicited.

Respectfully submitted,
J.C. PATENTS

Date: 2/28/2003

Jiawei Huang
Registration No. 43,330

4 Venture, Suite 250
Irvine, CA 92618
Tel.: (949) 660-0761
Fax: (949)-660-0809

Atty Docket No.: JCLA8066 Serial No.: 10/065,380

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In Tthe Title:

The Title has been amended as follows:

STORAGE CAPACITOR STRUCTURE AND LIQUID CRYSTAL DISPLAY DEVICE HAVING THE SAME

In the Claims:

Claims 7 and 9-15 have been canceled without prejudice, waiver, or disclaimer.

Claims 1-6 and 8 have been amended as follows:

1. (Once Amended) A unit cell in a liquid crystal display device [storage capacitor structure], the unit cell comprising:

a first capacitor electrode on a substrate;

a capacitor dielectric layer on the first capacitor electrode;

a second capacitor electrode on the capacitor dielectric layer, wherein the second capacitor electrode has a surface area smaller than the first capacitor electrode, to prevent overlapping with edges of the first capacitor electrode;

a passivation layer on the second capacitor electrode, wherein the passivation layer has an opening that exposes a portion of the second capacitor electrode; and

a pixel electrode layer on the passivation layer such that the pixel electrode layer and the second capacitor electrode are electrically connected through the opening in the passivation layer.

2. (Once Amended) The unit cell [capacitor structure] of claim 1, wherein an overlapping region between the first capacitor electrode and the second capacitor electrode is substantially equal to the surface area of the second capacitor electrode.

3. (Once Amended) The unit cell [capacitor structure] of claim 1, wherein the pixel electrode is further connected to a switching element.

4. (Once Amended) The unit cell [capacitor structure] of claim 1, wherein the pixel electrode is further connected to a thin film transistor.

5. (Once Amended) The unit cell [capacitor structure] of claim 1, wherein the first capacitor electrode is further connected to a common voltage.

6. (Once Amended) A storage capacitor structure in a unit cell of a liquid crystal display device, the storage capacitor structure comprising:

a first capacitor electrode on a substrate;

a capacitor dielectric layer on the substrate; and

a second capacitor electrode on the capacitor dielectric layer, wherein the edges of the second capacitor electrode are bounded within the edges of the first capacitor electrode.

8. (Once Amended) The capacitor structure of claim 6, wherein if residual conductive [residual] material is distributed along the edges of the first capacitor electrode, short-circuiting of the storage capacitor structure being prevented because no overlapping between the second capacitor electrode and the edges of the first capacitor electrode.

Claims 17-18 have been newly added.